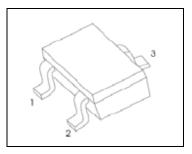


**Green Products** 

# **BAT54T/AT/CT/ST SCHOTTKY BARRIER DIODE**

#### Features:

- Low Forward Voltage Drop
- Fast Switching
- PN Junction Guard Ring for Transient and ESD Protection



BAT54T BAT54AT		BAT54CT	BAT54ST	
10-	1 ○──	1	1 ○ ▶	
<u></u> 3	3	3	○ 3	
2 0	2 ○  ◀	2 ○ →	2 ○ ◀	

#### Marking:

BA	\T54T	BAT54AT		BAT54CT		BAT54ST	
L 1	<u>L</u> 1	L2		L3	Ļ3	L4	L4

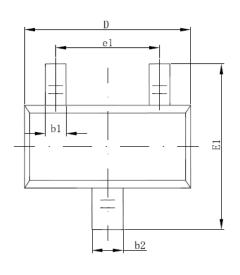
Solid dot = Green molding compound device, if none, the normal device.

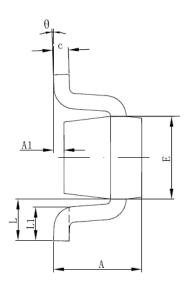
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •

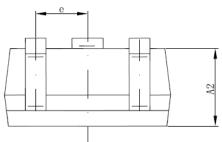


## Green Products

#### **Mechanical Dimensions: In mm/Inches**







Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016 REF.		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

**SOT-523** 

<sup>•</sup> China - Germany - Korea - Singapore - United States •

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### **Ordering Information:**

Device	Package	Shipping	
BAT54T/AT/CT/ST	SOT-523(Pb-Free)	3000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings @T<sub>A</sub>=25°C unless otherwise specified

Symbol	Parameter	Value	Unit	
$V_{RRM}$	Peak Repetitive Reverse Voltage	20	\/	
$V_{RWM}$	Working Peak Reverse Voltage	30	V	
V <sub>R(RMS)</sub>	RMS Reverse Voltage	21	V	
Io	Average Rectified Output Current	0.2	Α	
I <sub>FSM</sub>	Non-repetitive Peak Forward Surge Current @ t=8.3ms	600	mA	
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current @ t≤1s;δ≤0.5	300	mA	
P <sub>D</sub>	Power Dissipation	150	mW	
R <sub>⊝JA</sub>	Thermal Resistance from Junction to Ambient	667	°C/W	
T <sub>j</sub>	Junction Temperature	125	°C	
T <sub>stg</sub>	Storage Temperature	-55~+150	°C	

### Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

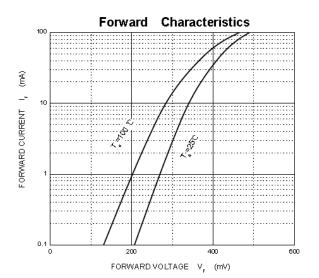
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Reverse voltage	$V_{(BR)}$	I <sub>R</sub> =100μA	30	-	-	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =25V	-	-	2	μA
Forward voltage	$V_{F}$	I <sub>F</sub> =1mA	-	-	0.32	V
		I <sub>F</sub> =10mA	-	-	0.4	
		I <sub>F</sub> =30mA	-	-	0.5	
		I <sub>F</sub> =100mA	-	-	1	
Total capacitance	C <sub>tot</sub>	V <sub>R</sub> =1V,f=1MHz	-	-	10	pF
Reverse recovery time	T <sub>rr</sub>	$I_F = I_R = 10$ mA, $Irr = 0.1 \times IR$ , $R_L = 100\Omega$	-	-	5	ns

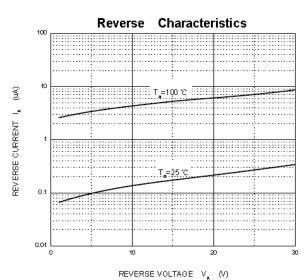
<sup>•</sup> China - Germany - Korea - Singapore - United States •

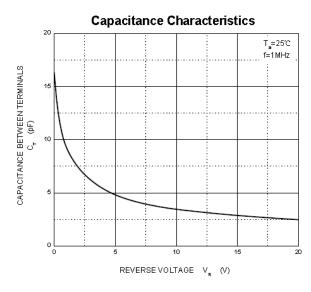
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •

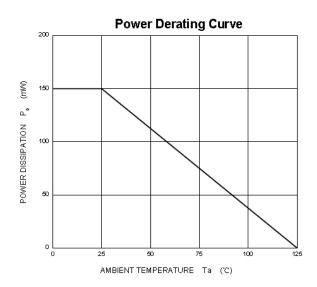












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